

深圳市晶泰源电子有限公司

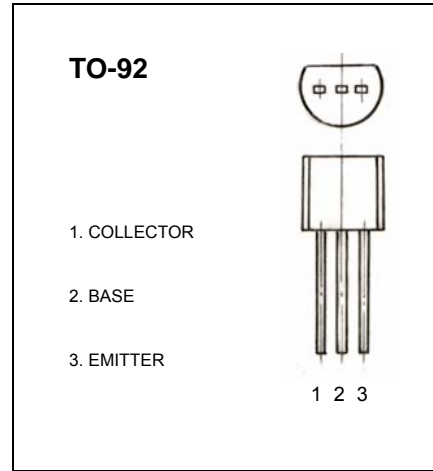
BC546/BC547/BC548 TRANSISTOR (NPN)

FEATURES

- High Voltage
- Complement to BC556,BC557,BC558

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	BC546 80	V
		BC547 50	
		BC548 30	
V_{CEO}	Collector-Emitter Voltage	BC546 65	V
		BC547 45	
		BC548 30	
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	100	mA
P_D	Total Device Dissipation	625	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	BC546 BC547 BC548	V_{CBO}	80 50 30		V
Collector-emitter breakdown voltage	BC546 BC547 BC548	V_{CEO}	65 45 30		V
Emitter-base breakdown voltage		V_{EBO}	6		V
Collector cut-off current	BC546 BC547 BC548	I_{CBO}		0.1	μA
Collector cut-off current	BC546 BC547 BC548	I_{CEO}		0.1	μA
Emitter cut-off current	BC546 BC547 BC548	I_{EBO}		0.1	μA
DC current gain	BC546 BC547 BC548 BC546A/BC547A/BC548A BC546B/BC547B/BC548B BC546C/BC547C/BC548C	h_{FE}	110 110 110 110 200 420	800 800 800 220 450 800	
Collector-emitter saturation voltage		$V_{CE(sat)}$		0.3	V
Base-emitter saturation voltage		$V_{BE(sat)}$		1.1	V
Transition frequency		f_T	150		MHz